

# 10V Drive Nch MOSFET

## R5011ANX

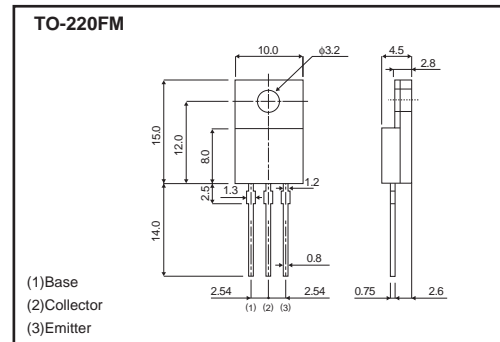
### ●Structure

Silicon N-channel MOSFET

### ●Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Gate-source voltage ( $V_{GS}$ ) guaranteed to be  $\pm 30V$ .
- 4) Drive circuits can be simple.
- 5) Parallel use is easy.

### ●Dimensions (Unit : mm)



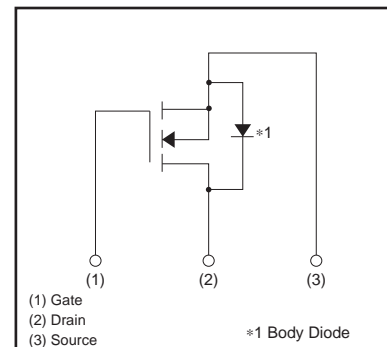
### ●Applications

Switching

### ●Packaging specifications

Type	Package	Bulk
	Code	-
	Basic ordering unit (pieces)	500
R5011ANX		○

### ●Inner circuit



### ●Absolute maximum ratings ( $T_a=25^\circ C$ )

Parameter	Symbol	Limits	Unit	
Drain-source voltage	$V_{DS}$	500	V	
Gate-source voltage	$V_{GS}$	$\pm 30$	V	
Drain current	Continuous	$I_D$ *3	$\pm 11$	A
	Pulsed	$I_{DP}$ *1	$\pm 44$	A
Source current (Body Diode)	Continuous	$I_S$ *3	11	A
	Pulsed	$I_{SP}$ *1	44	A
Avalanche Current	$I_{AS}$ *2	5.5	A	
Avalanche Energy	$E_{AS}$ *2	8.1	mJ	
Total power dissipation ( $T_c=25^\circ C$ )	$P_D$	50	W	
Channel temperature	$T_{ch}$	150	$^\circ C$	
Range of storage temperature	$T_{stg}$	-55 to +150	$^\circ C$	

\*1  $P_w \leq 10 \mu s$ , Duty cycle  $\leq 1\%$

\*2  $L = 500 \mu H$ ,  $V_{DD} = 50V$ ,  $R_G = 25 \Omega$ , Starting,  $T_{ch} = 25^\circ C$

\*3 Limited only by maximum temperature allowed

## Transistors

## ● Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to case	Rth(ch-c)	2.5	°C/W

## ● Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I <sub>GSS</sub>	–	–	±100	nA	V <sub>GS</sub> =±30V, V <sub>DS</sub> =0V
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	500	–	–	V	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	I <sub>DSS</sub>	–	–	100	μA	V <sub>DS</sub> =500V, V <sub>GS</sub> =0V
Gate threshold voltage	V <sub>GS(th)</sub>	2.5	–	4.5	V	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA
Static drain-source on-state resistance	R <sub>DS(on)</sub> *	–	0.38	0.5	Ω	I <sub>D</sub> =5.5A, V <sub>GS</sub> =10V
Forward transfer admittance	Y <sub>fs</sub>  *	3.5	–	–	S	I <sub>D</sub> =5.5A, V <sub>DS</sub> =10V
Input capacitance	C <sub>iss</sub>	–	1000	–	pF	V <sub>DS</sub> =25V
Output capacitance	C <sub>oss</sub>	–	400	–	pF	V <sub>GS</sub> =0V
Reverse transfer capacitance	C <sub>rss</sub>	–	35	–	pF	f=1MHz
Turn-on delay time	t <sub>d(on)</sub> *	–	26	–	ns	I <sub>D</sub> =5.5A, V <sub>DD</sub> ≒250V
Rise time	t <sub>r</sub> *	–	28	–	ns	V <sub>GS</sub> =10V
Turn-off delay time	t <sub>d(off)</sub> *	–	75	–	ns	R <sub>L</sub> =45.5Ω
Fall time	t <sub>f</sub> *	–	30	–	ns	R <sub>G</sub> =10Ω
Total gate charge	Q <sub>g</sub> *	–	30	–	nC	V <sub>DD</sub> ≒250V I <sub>D</sub> =11A
Gate-source charge	Q <sub>gs</sub> *	–	7	–	nC	V <sub>GS</sub> =10V
Gate-drain charge	Q <sub>gd</sub> *	–	12	–	nC	R <sub>L</sub> =22.7Ω / R <sub>G</sub> =10Ω

\* Pulsed

## ● Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V <sub>SD</sub> *	–	–	1.5	V	I <sub>S</sub> = 11A, V <sub>GS</sub> =0V

\* Pulsed

Transistors

●Electrical characteristic curves

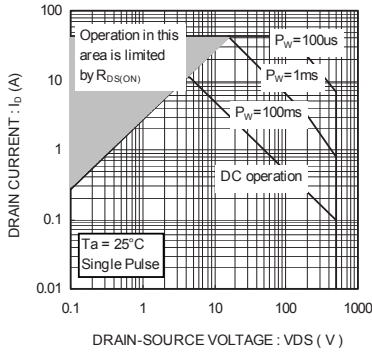


Fig.1 Maximum Safe Operating Area

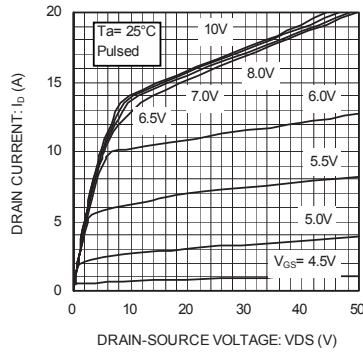


Fig.2 Typical Output Characteristics( I )

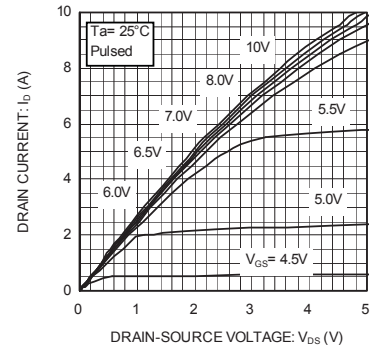


Fig.3: Typical Output Characteristics( II )

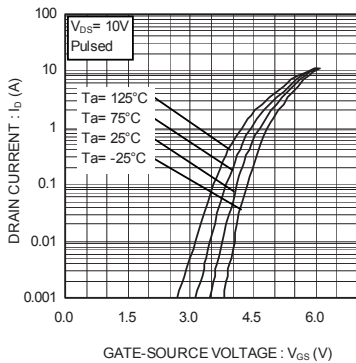


Fig.4 Typical Transfer Characteristics

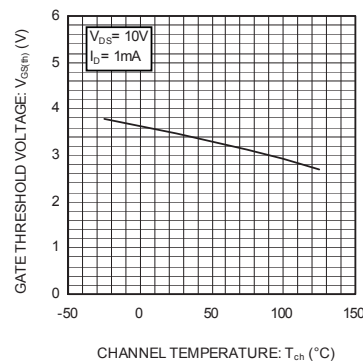


Fig.5 Gate Threshold Voltage vs. Channel Temperature

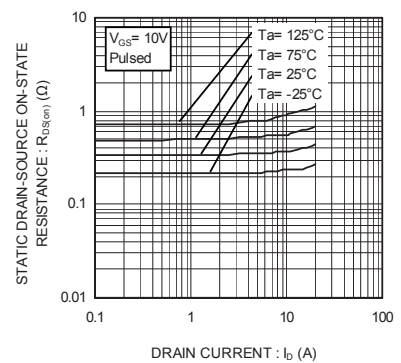


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current

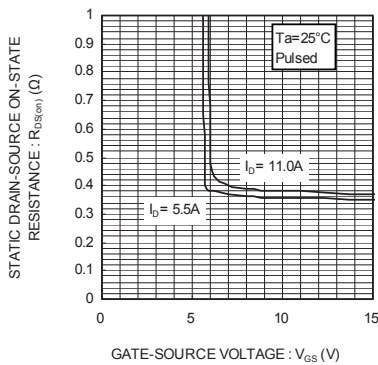


Fig.7 Static Drain-Source On-State Resistance vs. Gate Source Voltage

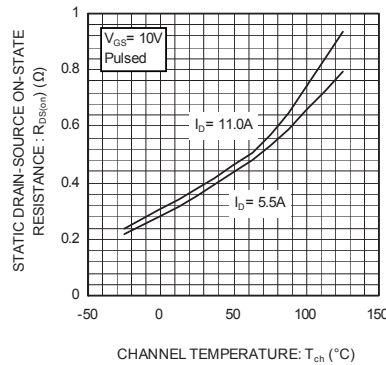


Fig.8 Static Drain-Source On-State Resistance vs. Channel Temperature

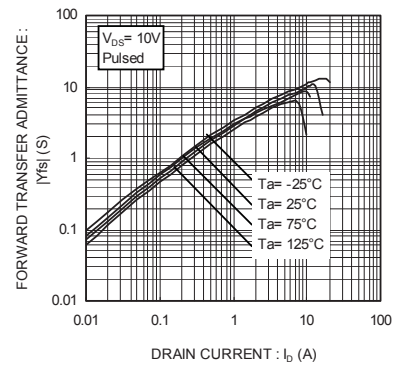


Fig.9 Forward Transfer Admittance vs. Drain Current

Transistors

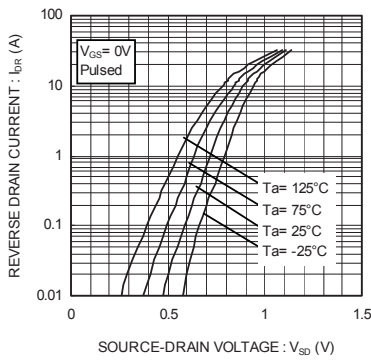


Fig. 10 Reverse Drain Current vs. Source-Drain Voltage

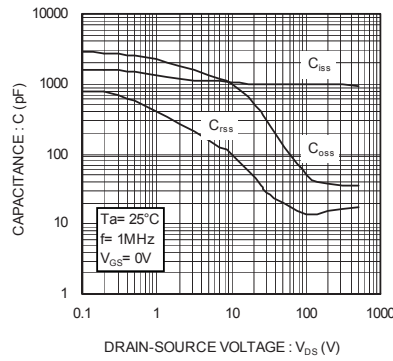


Fig. 11 Typical Capacitance vs. Drain-Source Voltage

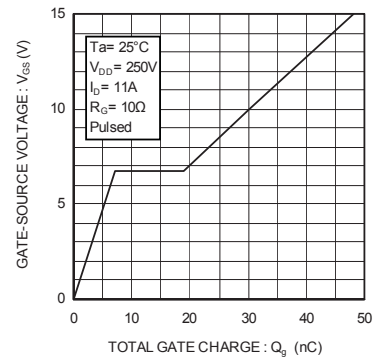


Fig. 12 Dynamic Input Characteristics

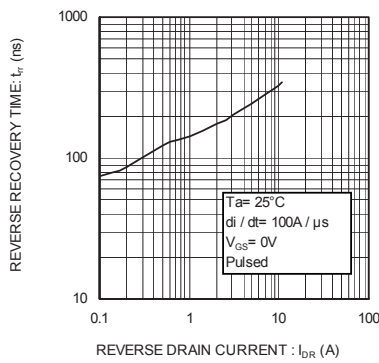


Fig. 13 Reverse Recovery Time vs. Reverse Drain Current

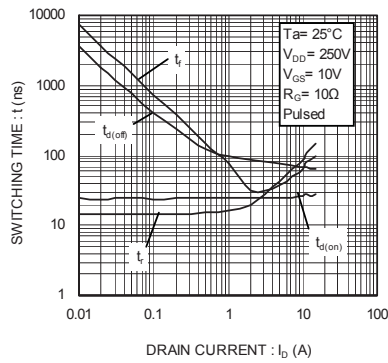


Fig. 14 Switching Characteristics

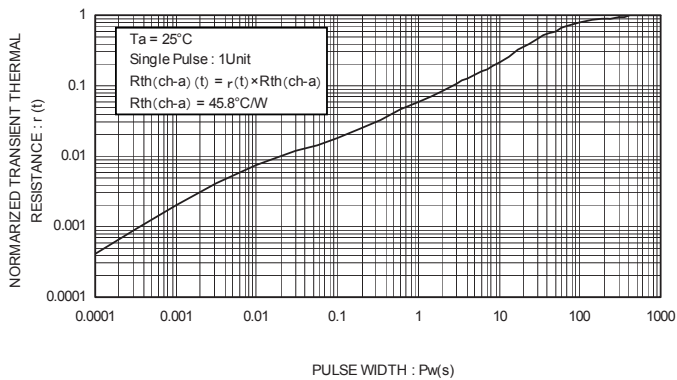


Fig. 15 Normalized Transient Thermal Resistance vs. Pulse Width

Transistors

●Switching characteristics measurement circuit

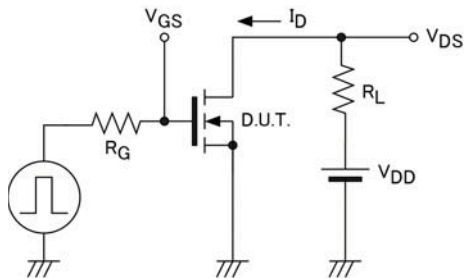


Fig.1-1 Switching Time Measurement Circuit

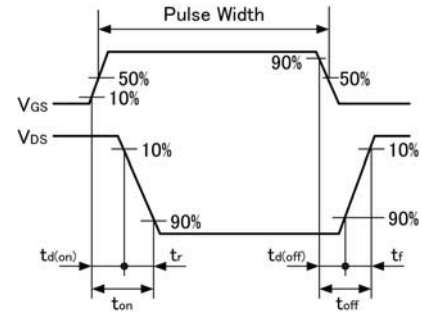


Fig.1-2 Switching Waveforms

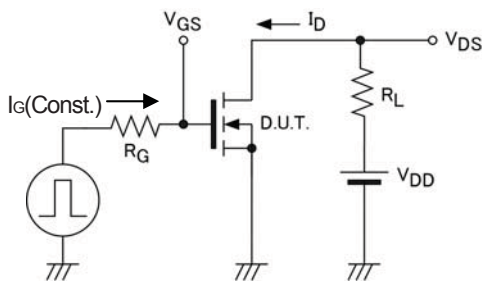


Fig.2-1 Gate Charge Measurement Circuit

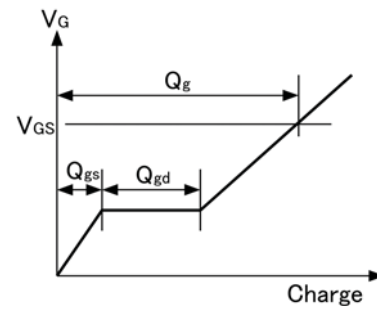


Fig.2-2 Gate Charge Waveform

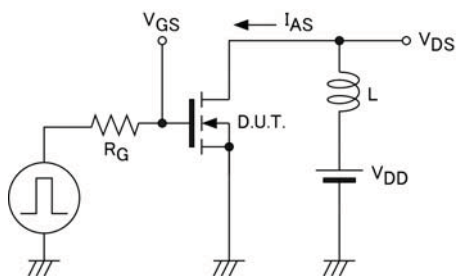


Fig.3-1 Avalanche Measurement Circuit

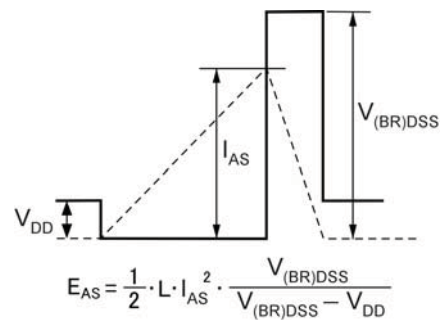


Fig.3-2 Avalanche Waveform

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